

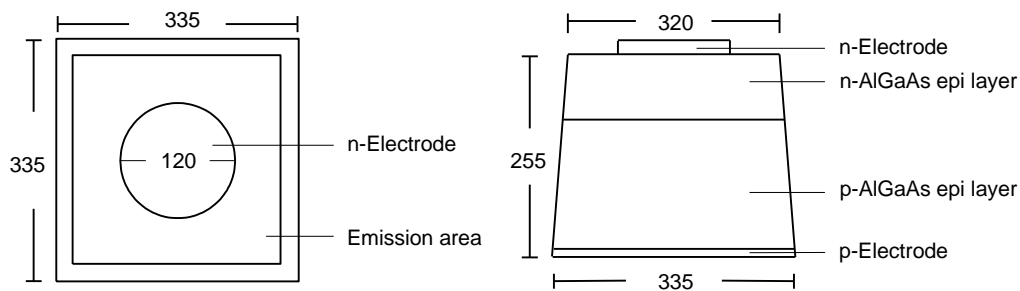
### Features :

- N Side Up

### Typical Applications :

- Industrial Infrared Equipment

### Outline Dimensions : (Unit: $\mu\text{m}$ )



### Physical Structure :

Chip dimension	Chip size	335 $\mu\text{m}$ x 335 $\mu\text{m}$
	Thickness	255 $\mu\text{m}$
	Emission area	320 $\mu\text{m}$
	Bonding pad	120 $\mu\text{m}$
Electrode	Top: N (cathode)	Gold (Aluminum optional)
	Backside: P (anode)	Gold alloy
Surface condition	Smooth	

### Electro-Optical Characteristics : ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20 \text{ mA}$	-	1.36	1.55	V
		$I_F = 100 \text{ mA}$	-	1.72	-	
Reverse Voltage	$V_R$	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	$\lambda_p$	$I_F = 20 \text{ mA}$	-	880	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	70	-	nm
Radiant Power	$P_o$	$I_F = 20 \text{ mA}$	0.40	0.94	-	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

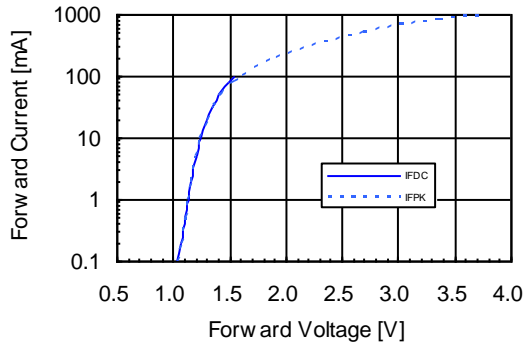


Fig 2. Relative Radiant Power vs. Wavelength

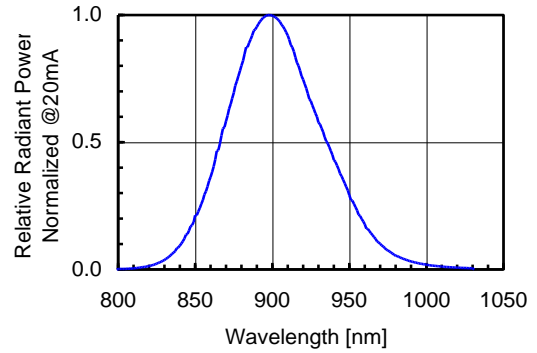


Fig 3. Relative Radiant Power vs. Forward DC Current

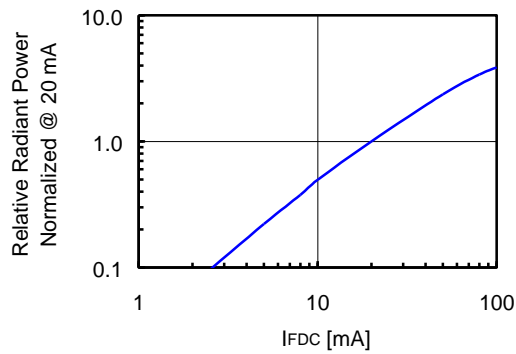


Fig 4. Relative Radiant Power vs. Forward Peak Current

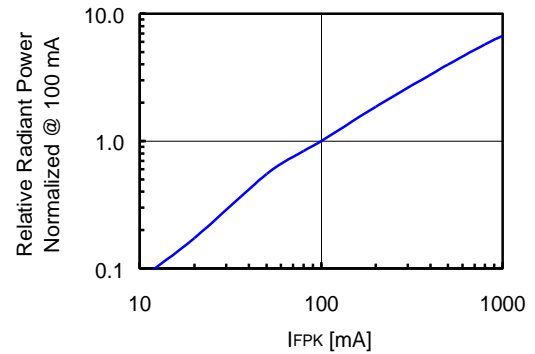


Fig 5. Forward DC Voltage vs. Temperature

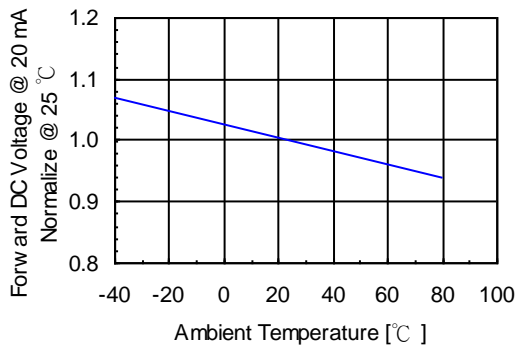


Fig 6. Relative Radiant Power vs. Temperature

